Docket No.: 57454-964 **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hideto HIDAKA

Serial No.: Divisional of Appl. No.

09/832,025 : Group Art Unit:

Filed: July 09, 2003 : Examiner:

For: THIN FILM MAGNETIC MEMORY DEVICE HAVING A HIGHLY INTEGRATED

MEMORY ARRAY

INFORMATION DISCLOSURE STATEMENT

Mail Stop Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 09/832,025, filed April 11, 2001, which is relied upon for an

09/832,025

earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

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Date: July 9, 2003

- INFORMATION DISCLOSURE CITATION IN AN - APPLICATION					ATTY. DOCKET NO. 57454-964		SERIAL NO. Divisional of Appl. No. 09/832,025				
					APPLICANT Hideto HIDAKA						
(PTO-1449)					FILING DATE July 09, 2003		GROUP				
19. 15 · 14 · 14 · 14 · 14 · 14 · 14 · 14 ·	B Ann	, p		U.S. PATEN	NT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Num	Document Number ber-Kind Code2 (If known)	Publication Dat MM-DD-YYYY		Name of Patentee or Applicant of Cited Document			Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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								Yes	No		
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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.									
			Roy Scheuerlein, et al. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell", ISSCC Digest of Technical Papers, TA7.2, February 2000, pp. 128-129, 94-95 and 409.								
	M. Durlam et al., "Nonvolatile RAM Based on Magnetic Tunnel Junction Elements", ISSCC Digest of Technical Papers, TA7.3, February 2000, pp. 130-131, 96-97, 410-411.										
EXAMINER DATE CONSIDERED											

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.